

Abstract of Disclosure

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METHOD FOR FABRICATING TRANSISTOR

10 A method for fabricating a transistor includes providing a gate structure on a main surface of a semiconductor substrate; lining the gate structure and the main surface of the semiconductor substrate with a screen layer; performing a source/drain ion implantation to implant dopants into the semiconductor substrate, thereby forming heavily doped source/drain regions; and performing a salicide block (SAB) process comprising depositing a silicon nitride layer overlying the screen layer, and selectively etching the silicon nitride layer and the
15 screen layer to form a SAB pattern.

Figure 9

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